

**Features**

- n Center amplifying gate
- n Metal case with ceramic insulator
- n Low on-state and switching losses

**Typical Applications**

- n AC controllers
- n DC and AC motor control
- n Controlled rectifiers

<b>Part No. Y89KPE-KT84dT</b>			
<b>I<sub>T(AV)</sub></b>	<b>4000A</b>		
<b>V<sub>DRM</sub>, V<sub>RRM</sub></b>	<b>1200V</b>	<b>1400V</b>	
	<b>1600V</b>	<b>1800V</b>	

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT	
				Min	Type	Max		
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T <sub>c</sub> =70°C	125			4000	A
			T <sub>c</sub> =85°C	125			3400	A
			T <sub>c</sub> =55°C	125			4800	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	125	1200		1800	V	
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			250	mA	
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave V <sub>R</sub> =0.6V <sub>RRM</sub>	125			64	kA	
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination					20480	10 <sup>3</sup> A <sup>2</sup> s	
V <sub>TO</sub>	Threshold voltage		125			0.83	V	
r <sub>T</sub>	On-state slope resistance					0.09	mΩ	
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =5000A, F=40kN	25			1.80	V	
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			1000	V/μs	
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 50%V <sub>DRM</sub> Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A	125			200	A/μs	
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =2000A, tp=4000μs, di/dt=-20A/μs, V <sub>R</sub> =100V	125		1600		μC	
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	40		300	mA	
V <sub>GT</sub>	Gate trigger voltage			0.8		3.0	V	
I <sub>H</sub>	Holding current			20		300	mA	
I <sub>L</sub>	Latching current					1000	mA	
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.3	V	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	double side cooled Clamping force 40kN				0.007	°C/W	
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink					0.003		
F <sub>m</sub>	Mounting force			63		84	kN	
T <sub>vj</sub>	Junction temperature			-40		125	°C	
T <sub>stg</sub>	Stored temperature			-40		140	°C	
W <sub>t</sub>	Weight				1920		g	
Outline	KT84dT							

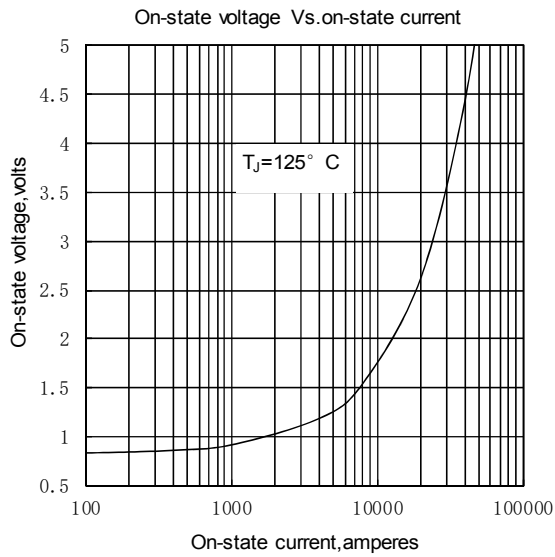


Fig.1

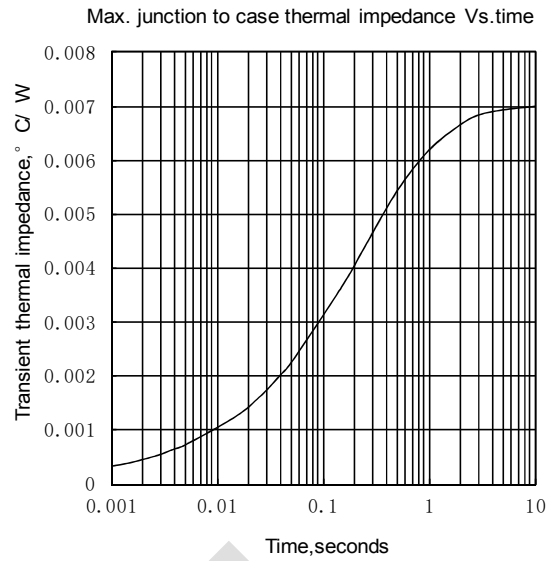


Fig.2

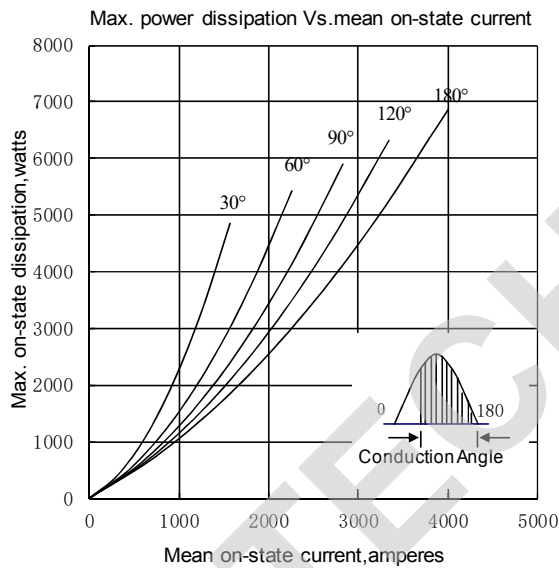


Fig.3

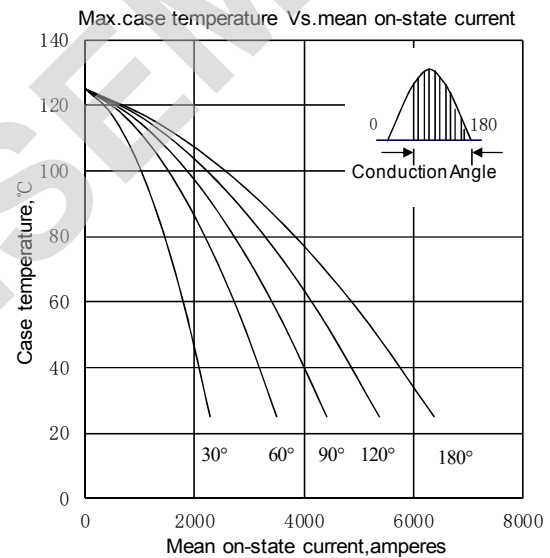


Fig.4

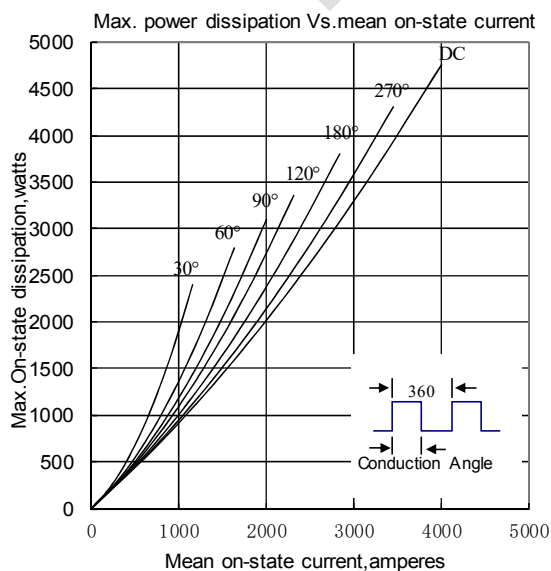


Fig.5

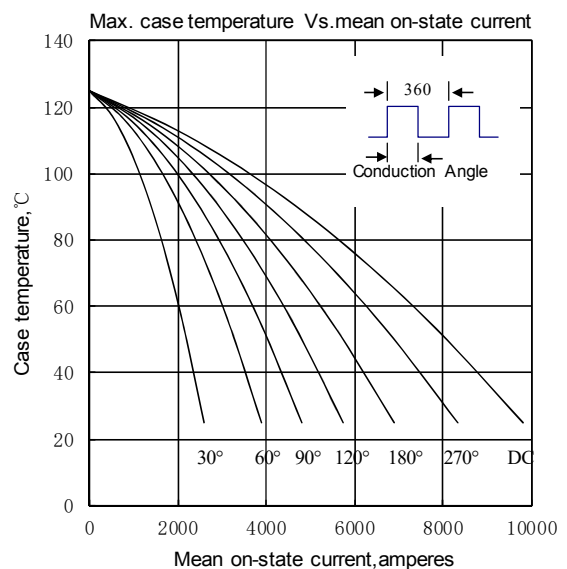


Fig.6

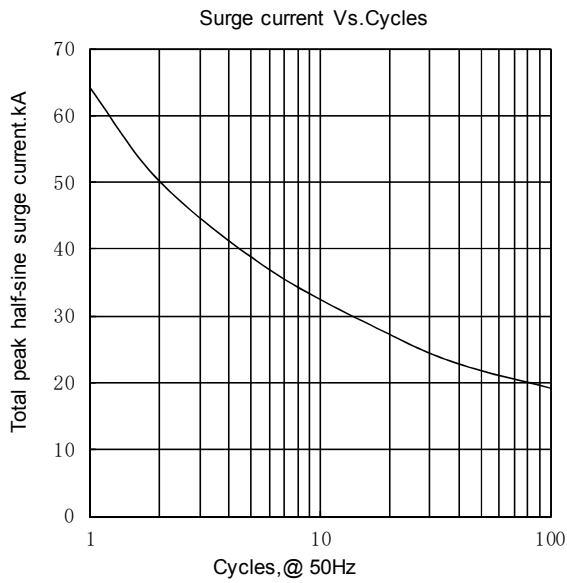


Fig.7

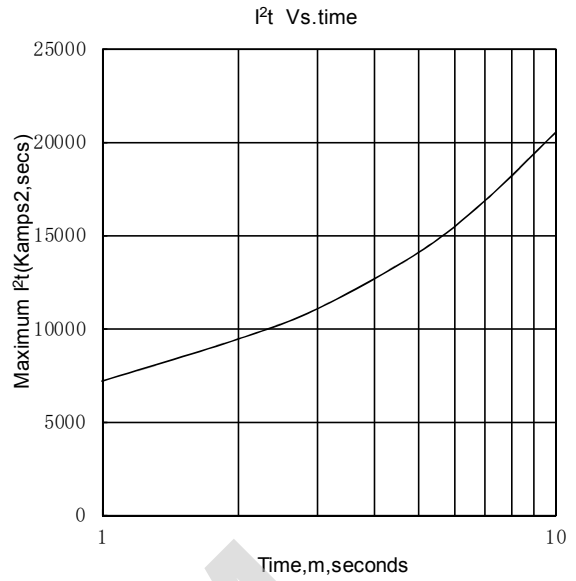


Fig.8

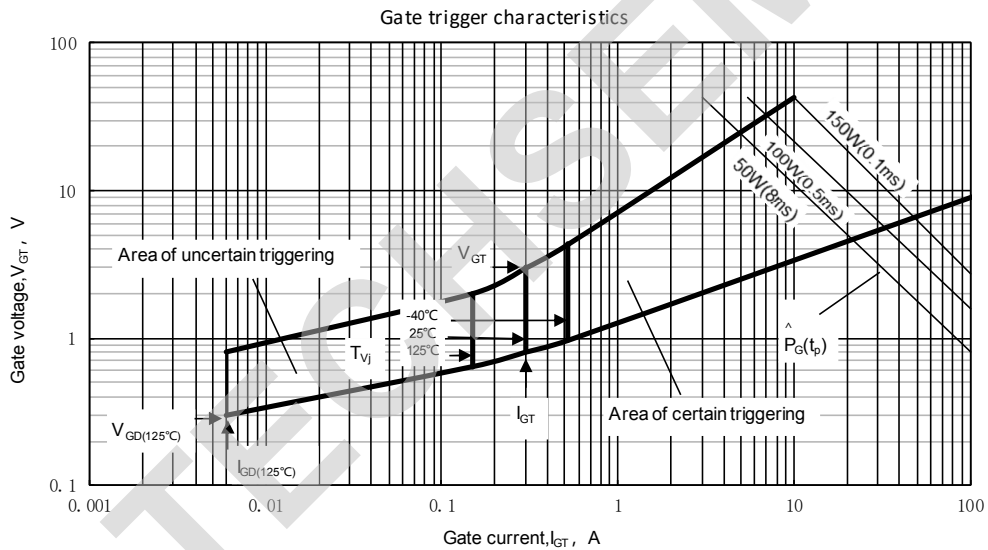
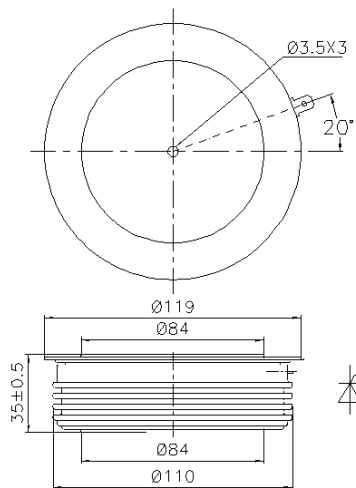


Fig.9

Outline:



TECHSEM reserves the right to change specifications without notice.